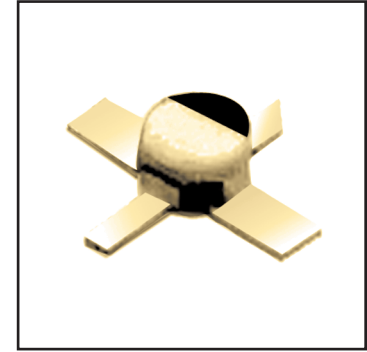


FHX76LP

Super Low Noise HEMT

FEATURES

- Low Noise Figure: NF=0.40dB (Typ.)@f=12GHz
- High Associated Gain: Gas=13.5dB (Typ.)@f=12GHz
- High Reliability
- Small Size SMT Package
- Tape and Reel Packaging Available



DESCRIPTION

The FHX76LP is a low noise SuperHEMT™ product designed for DBS applications. This device uses a small ceramic package that is optimized for high volume cost driven requirements.

Eudyna's stringent Quality Assurance Program assures the highest reliability and consistent performance.

ABSOLUTE MAXIMUM RATINGS (Ambient Temperature Ta = 25°C)

Parameter	Symbol	Condition	Rating	Unit
Drain-Source Voltage	V _{DS}		3.5	V
Gate-Source Voltage	V _{GS}		-3.0	V
Total Power Dissipation	P _t	Note	180	mW
Storage Temperature	T _{STG}		-65 to 150	°C
Channel Temperature	T _{CH}		150	°C

Note: Mounted on Al₂O₃ board (30 x 30 x 0.65mm)

Eudyna recommends the following conditions for the reliable operation of GaAs FETs:

1. The drain-source operating voltage (V_{DS}) should not exceed 2 volts.
2. The forward and reverse gate currents should not exceed 0.2 and -0.05 mA respectively with gate resistance of 4000Ω.
3. The operating channel temperature (T_{ch}) should not exceed 80°C.

ELECTRICAL CHARACTERISTICS (Ambient Temperature Ta=25°C)

Item	Symbol	Conditions	Limits			Unit
			Min.	Typ.	Max.	
Saturated Drain Current	I _{DSS}	V _{DS} = 2V, V _{GS} =0V	10	30	60	mA
Transconductance	gm	V _{DS} = 2V, I _{DS} =10mA	35	50	-	mS
Pinch-Off Voltage	V _p	V _{DS} = 2V, I _{DS} =1mA	-0.1	-0.7	-1.5	V
Gate-Source Breakdown Voltage	V _{GSO}	I _{GS} = -10μA	-3.0	-	-	V
Noise Figure	NF	V _{DS} = 2V, I _{DS} = 10mA, f=12GHz	-	0.40	0.50	dB
Associated Gain	Gas		12.0	13.5	-	dB
Thermal Resistance	R _{th}	Channel to Case	-	300	400	°C/W

CASE STYLES: LP

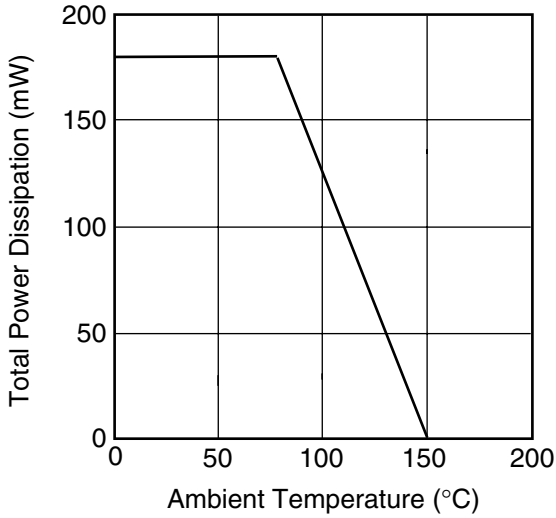
Note: RF parameters for LP devices are measured on a sample basis as follows:

Lot qty.	Sample qty.	Accept/Reject
1200 or less	125	(0,1)
1201 to 3200	200	(0,1)
3201 to 10000	315	(1,2)
10001 or over	500	(1,2)

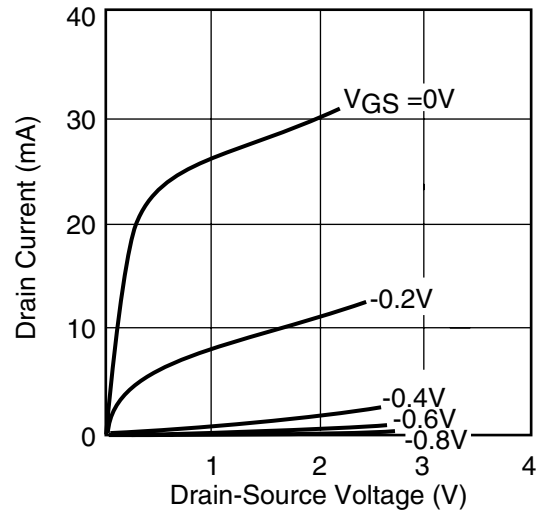
FHX76LP

Super Low Noise HEMT

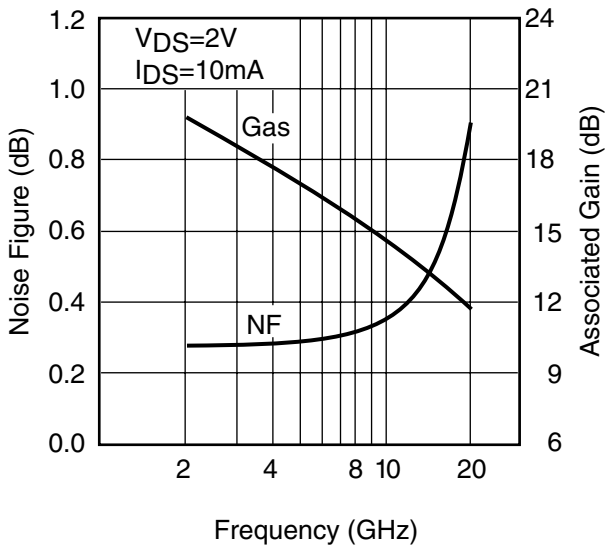
POWER DERATING CURVE



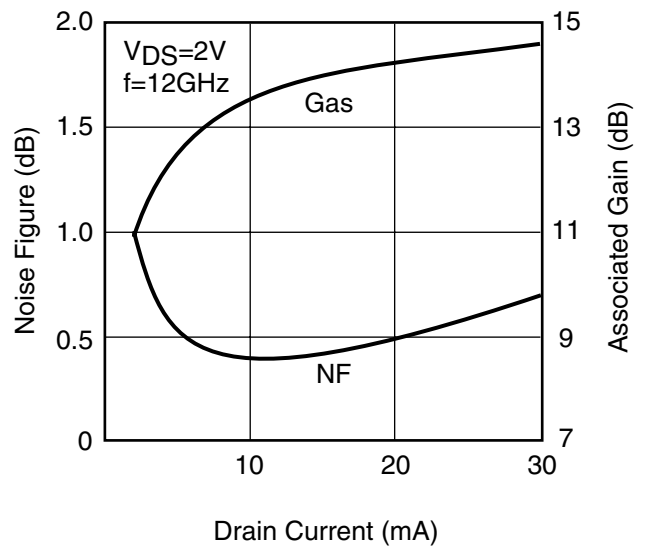
DRAIN CURRENT vs. DRAIN-SOURCE VOLTAGE



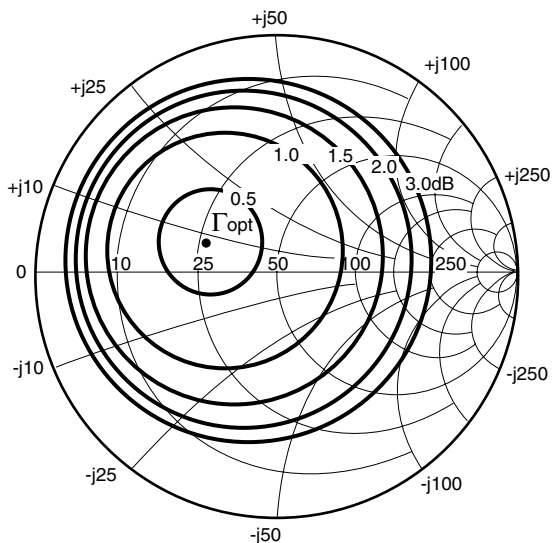
NF & Gas vs. FREQUENCY



NF & Gas vs. I_{DS}



TYPICAL NOISE FIGURE CIRCLE



f=12GHz
 $V_{DS}=2V$
 $I_{DS}=10mA$

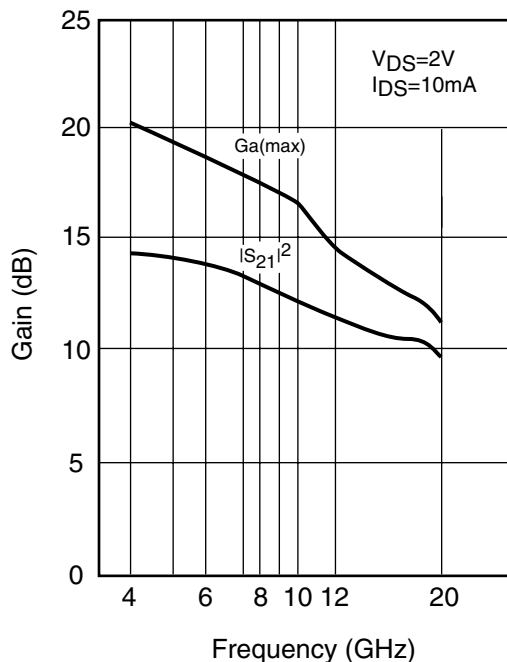
$\Gamma_{opt}=0.32 \angle 153.8^\circ$
 $R_n/50=0.06$
 $NF_{min}=0.40dB$

NOISE PARAMETERS

$V_{DS}=2V, I_{DS}=10MA$

Freq. (GHz)	Γ_{opt}		NFmin (dB)	Rn/50
	(MAG)	(ANG)		
2	0.79	12.5	0.28	.24
4	0.62	30.0	0.29	.20
6	0.50	54.1	0.30	.16
8	0.41	83.6	0.32	.12
10	0.35	117.3	0.35	.08
12	0.32	153.8	0.40	.06
14	0.30	-168.0	0.48	.06
16	0.29	-129.5	0.60	.09
18	0.29	-91.8	0.72	.14
20	0.29	-56.3	0.91	.19

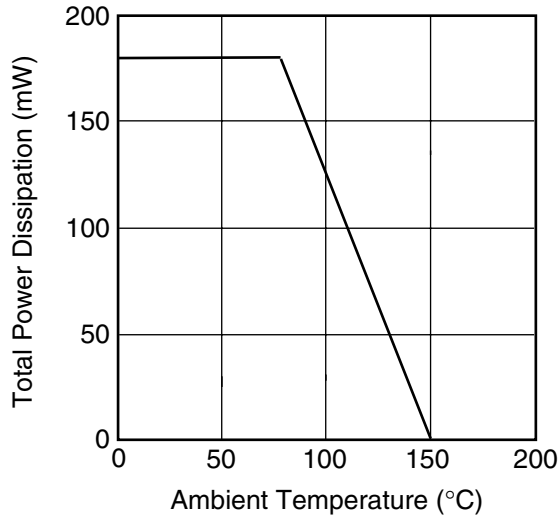
Ga(max) AND $|S_{21}|$ vs. FREQUENCY



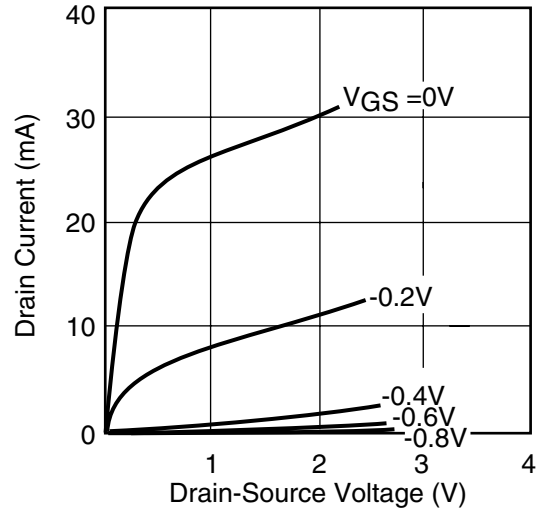
FHX76LP

Super Low Noise HEMT

POWER DERATING CURVE



DRAIN CURRENT vs. DRAIN-SOURCE VOLTAGE



S-PARAMETERS

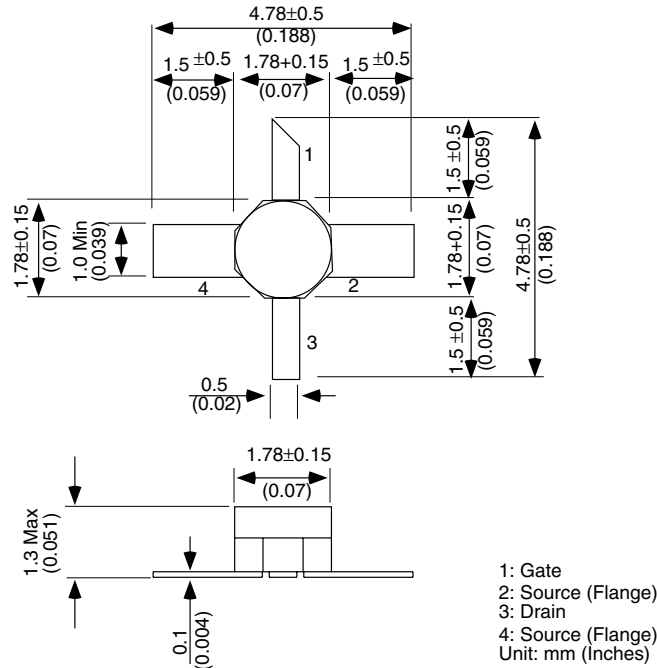
V_{DS} = 2V, I_{DS} = 10mA

FREQUENCY (MHZ)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
1000	.987	-14.8	5.535	164.2	.014	80.2	.585	-11.4
2000	.965	-29.4	5.463	148.8	.027	70.2	.567	-22.9
3000	.925	-44.6	5.334	133.2	.041	57.7	.538	-34.7
4000	.878	-58.3	5.154	118.8	.049	50.0	.511	-45.2
5000	.828	-72.9	5.019	104.3	.059	40.6	.480	-56.4
6000	.776	-87.8	4.825	89.8	.067	32.4	.446	-68.4
7000	.719	-102.8	4.606	75.6	.075	23.2	.413	-80.6
8000	.669	-116.6	4.354	61.9	.079	15.2	.394	-92.6
9000	.631	-129.4	4.130	49.5	.083	6.3	.374	-102.4
10000	.590	-141.7	3.982	37.0	.086	.2	.365	-112.5
11000	.548	-155.3	3.849	24.7	.088	-7.6	.335	-121.9
12000	.507	-169.6	3.689	12.4	.091	-14.2	.323	-134.1
13000	.482	177.0	3.545	-.2	.095	-20.8	.313	-145.0
14000	.459	164.7	3.425	-11.9	.096	-28.7	.315	-155.9
15000	.439	152.3	3.330	-24.4	.098	-36.4	.324	-165.4
16000	.419	138.7	3.264	-37.1	.102	-44.1	.322	-174.3
17000	.404	123.9	3.238	-50.3	.103	-54.6	.321	175.4
18000	.383	107.3	3.176	-63.5	.108	-63.4	.316	165.3
19000	.377	93.2	3.101	-78.0	.105	-74.5	.320	153.2
20000	.348	76.5	3.028	-92.3	.110	-87.6	.301	146.1

NOTE:* The data includes bonding wires.

n: number of wires Gate n=1 (0.1mm length, 25µm Dia Au wire)
 Drain n=1 (0.1mm length, 25µm Dia Au wire)
 Source n=4 (0.2mm length, 25µm Dia Au wire)

Case Style "LP" Metal-Ceramic Package



For further information please contact:

Eudyna Devices USA Inc.

2355 Zanker Rd.
San Jose, CA 95131-1138, U.S.A.
TEL: (408) 232-9500
FAX: (408) 428-9111
www.us.eudyna.com

Eudyna Devices Europe Ltd.

Network House
Norreys Drive
Maidenhead, Berkshire SL6 4FJ
United Kingdom
TEL: +44 (0) 1628 504800
FAX: +44 (0) 1628 504888

Eudyna Devices Asia Pte Ltd.

Hong Kong Branch
Rm. 1101, Ocean Centre, 5 Canton Rd.
Tsim Sha Tsui, Kowloon, Hong Kong
TEL: +852-2377-0227
FAX: +852-2377-3921

Eudyna Devices Inc.

Sales Division
1, Kanai-cho, Sakae-ku
Yokohama, 244-0845, Japan
TEL: +81-45-853-8156
FAX: +81-45-853-8170

CAUTION

Eudyna Devices Inc. products contain **gallium arsenide (GaAs)** which can be hazardous to the human body and the environment. For safety, observe the following procedures:

- Do not put this product into the mouth.
- Do not alter the form of this product into a gas, powder, or liquid through burning, crushing, or chemical processing as these by-products are dangerous to the human body if inhaled, ingested, or swallowed.
- Observe government laws and company regulations when discarding this product. This product must be discarded in accordance with methods specified by applicable hazardous waste procedures.

Eudyna Devices Inc. reserves the right to change products and specifications without notice. The information does not convey any license under rights of Eudyna Devices Inc. or others.

© 2004 Eudyna Devices USA Inc.
Printed in U.S.A.